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Contents

- v Authors
- vii Conference Committee

NANOWIRE DEVICES AND CHARACTERIZATION

10929 05 MBE-grown GaAs/AlGaAs multiple quantum wells on Ge substrate [10929-4]

QUANTUM DOT DEVICES

10929 0C MBE-grown InGaAs/GaAs quantum-dots on Ge substrate: An idea towards optoelectronic integration on silicon [10929-11]

QUANTUM DOTS I

- 10929 OE Effect of vertical coupling on the performance of mid-infrared InAs-QDIP [10929-13]
- 10929 OF Auger recombination-induced neutralization and stretched exponential recharging in an InAs quantum dot [10929-14]
- 10929 0G Improvement in operating temperature of InAs/GaAs quantum-dots-based photodetectors by varying position of localized carriers in active region [10929-15]

QUANTUM DOTS II

- 10929 01 Coulomb-induced recombination dynamics in magnetically doped type-IIb quantum dots [10929-17]
- 10929 0K Influence of modulation doping on p-i-p quantum-dots (InAs/GaAs)-based infrared detector performance [10929-19]

PHYSICS OF NANOSTRUCTURES

10929 0N Tailoring and controlling fermionic properties in heterogenous quantum-dot colloidal solutions [10929-22]

COLLOIDAL QUANTUM DOTS

- 10929 0U Synthesis of ITO nanocrystals in mesoporous silica glasses and application for enhanced downconversion fluorescence of Er³⁺/Yb³⁺ ions [10929-29]
- 10929 0V Evaluation of pH-tuned ZnO down-shifting photoluminescent quantum dots and their influence on single-crystal silicon solar cells [10929-30]
- 10929 0X Impact of a time gate to the purity of single photons emitted from colloidal quantum dots [10929-32]

POSTER SESSION

- 10929 0Z Analysis of strain relaxation and dark current minimization in In(Ga)As QDIP with In0.15Ga0.85As/GaAs capping [10929-34]
- 10929 10 Investigation of carrier-confinement and dark current minimization in In_{0.5}Ga_{0.5}As quantum dot infrared photodetector with the incorporation of In_{0.21}AI0.21Ga_{0.58}As/GaAs capping [10929-35]
- 10929 11 Impact of ultra-thin quaternary capping on modulation doped p-i-p quantum dots (InAs/GaAs) based infrared detector [10929-36]
- 10929 12 Impact of ternary capping on p-i-p InAs/GaAs quantum-dot infrared photodetectors [10929-37]

Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Aanand, Abhijeet, 0G, 0K Álvarez-Ramos, Mario Enrique, OV Ayón, Arturo A., 0N, 0V Cartwright, A. N., Ol Chakrabarti, Subhananda, 05, 0C, 0E, 0G, 0K, 0Z, 10, 11, 12 Chatterjee, Arka, OC Chavan, Vinayak, OE, OG, OK, OZ, 10 Chen, Disheng, OF Chen, Ping, OU Chou, W.-C., 0 Dai, Nengli, 0U Das, Debabrata, OC, OE, OG, OK, OZ, 10, 11, 12 Demircan, Samet, OF Deviprasad, Vidya P., 0G, 0K, 11, 12 Fan, W. C., 01 Flagg, Edward B., OF Flores-Pacheco, Alvaro, 0V García-Monge, Itzel Alexia, 0N García-Monge, Janeth Alexandra, 0N Ghadi, Hemant, 0G, 0K, 11, 12 lhara, T., OX Isaac, Samantha D., OF Kumar, Raman, 05, 0C, 0E, 0Z, 10 Kumar, Ravinder, 05, 0C, 0E, 0Z, 10 Kumar Pal, Samir, OC Lander, Gary R., OF Li, Jinyan, OU Miki, S., OX Montes-Bojórquez, José Raul, OV Mukai, Toshikazu, 09 Panda, Debiprasad, 05, 0C, 0E, 0G, 0K, 0Z, 10, 11, 12 Raut, Pravin, OG, OK Saha, Jhuma, OC Sheshadri, Sreedhara, OE, OZ, 10 Solomon, Glenn S., 0F Tarasek, S., Ol Terai, H., OX Thomay, T., Ol Tongbram, Binita, 05, 0C Upadhyay, Sourabh, OC Villa-Bracamonte, Maria Fernanda, ON Yamada, T., OX Yang, Lvyun, OU Zepeda-Galvez, Juan Adrian, ON

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- 8 Colloidal Quantum Dots
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